

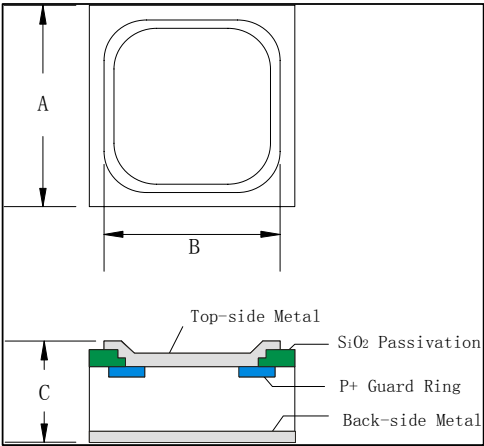
SB120S

SCHOTTKY DIE SPECIFICATION	TYPE: SB120S
General Description: 20 V 1 A (<input checked="" type="checkbox"/> Standard <input type="checkbox"/> Low) VF,	(<input checked="" type="checkbox"/> Single <input type="checkbox"/> Dual) Anode

ELECTRICAL CHARACTERISTICS	SYM	Spec. Limit	UNIT
DC Blocking Voltage @ IR=1mA	VRRM	20	Volt
Average Rectified Forward Current	IFAV	1	Amp
Maximum Instantaneous Forward Voltage			
@ 1 Ampere, Ta=25 °C	VF MAX	0.430	Volt
Reverse current			
@ VR= 23 Volt, Ta=25 °C	IR MAX	0.100	mA
MAXIMUM RATINGS			
Nonrepetitive Peak Surge Current	IFSM	32	Amp
Operating Junction Temperature	Tj	125	°C
Storage Temperature	TSTG	-50 to +150	°C

Specifications apply to die only. Actual performance may degrade when assembled.
 We do not guarantee device performance after assembly.
 Data sheet information is subjected to change without notice.

DICE OUTLINE DRAWING



DIM	ITEM	µm	Mil
A	Die Size	762	30.00
B	Top Metal Pad Size	678	26.69
C	Die	Thickness (Min)	280 11.02
		Thickness (Max)	300 11.81
	Wafer	Thickness (Min)	190 7.48
		Thickness (Max)	210 8.27

PS:
 (1) Cutting street width is around 16µm (0.62mil).
 (2) Both of top-side and back-side metals are Ti/Ni/Ag.